

International **IR** Rectifier

SMPS MOSFET

PD - 96064

IRLR7811WCPbF

HEXFET® Power MOSFET

Applications

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- Lead-Free

Benefits

- Very Low RDS(on) at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current

V _{DSS}	R _{DS(on)} max	Q _g
30V	10.5mΩ	19nC



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	64 [ⓐ]	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	45 [ⓐ]	
I _{DM}	Pulsed Drain Current [ⓐ]	260	
P _D @ T _C = 25°C	Power Dissipation	71	W
P _D @ T _A = 100°C	Power Dissipation*	1.5	
	Linear Derating Factor	0.48	W/°C
V _{GS}	Gate-to-Source Voltage	±12	V
T _J	Operating Junction and	-55 to +175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	2.1	°C/W
R _{θJA}	Junction-to-Ambient (PCB mount)*	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

Notes ① through ④ are on page 9
 www.irf.com

IRLR7811WCPbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	27	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ④
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.8	10.5	mΩ	$V_{GS} = 10V, I_D = 15A$ ④
		—	7.0	15		$V_{GS} = 4.5V, I_D = 12A$
$V_{GS(th)}$	Gate Threshold Voltage	—	1.5	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-5.0	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	30	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -12V$
g_{fs}	Forward Transconductance	58	—	—	S	$V_{DS} = 15V, I_D = 12A$
Q_g	Total Gate Charge Control Fet	—	21	31	nC	
Q_{gs1}	Pre-V _{th} Gate-Source Charge	—	5.0	—		
Q_{gs2}	Post-V _{th} Gate-Source Charge	—	1.7	—		
Q_{gd}	Gate-to-Drain Charge	—	6.6	—		
Q_{godr}	Gate Charge Overdrive	—	5.5	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	8.3	—		
Q_g	Total Gate Charge Sync Fet	—	17	—		
Q_{oss}	Output Charge	—	10	—		
R_g	Gate Resistance	—	1.6	—		
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	$V_{DD} = 16V, V_{GS} = 4.5V$ ④ $I_D = 12A$ Clamped Inductive Load
t_r	Rise Time	—	4.8	—		
$t_{d(off)}$	Turn-Off Delay Time	—	11	—		
t_f	Fall Time	—	23	—		
C_{iss}	Input Capacitance	—	2260	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	420	—		
C_{rss}	Reverse Transfer Capacitance	—	180	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	140	mJ
I_{AR}	Avalanche Current③	—	12	A
E_{AR}	Repetitive Avalanche Energy④	—	7.1	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	64	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	260		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 12A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	30	45	ns	$T_J = 25^\circ\text{C}, I_F = 12A$
Q_{rr}	Reverse Recovery Charge	—	27	41	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

International
IR Rectifier

IRLR7811WCPbF

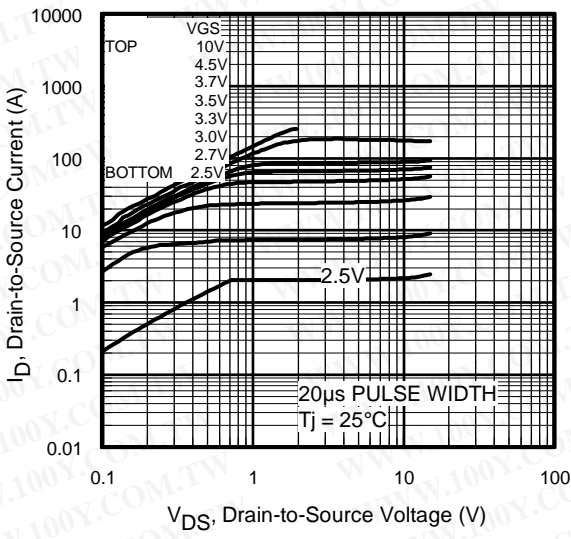


Fig 1. Typical Output Characteristics

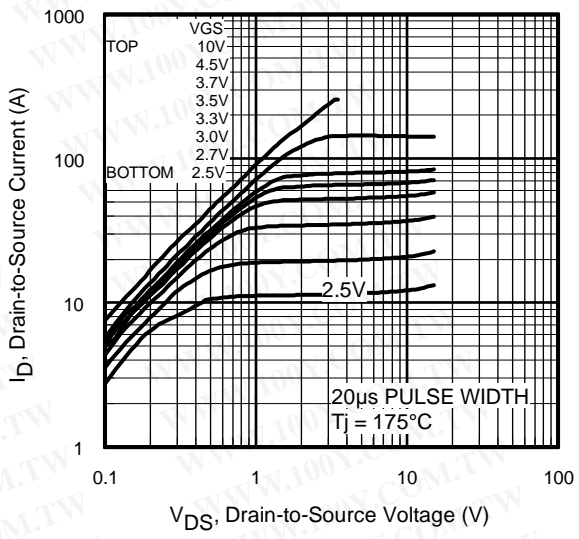


Fig 2. Typical Output Characteristics

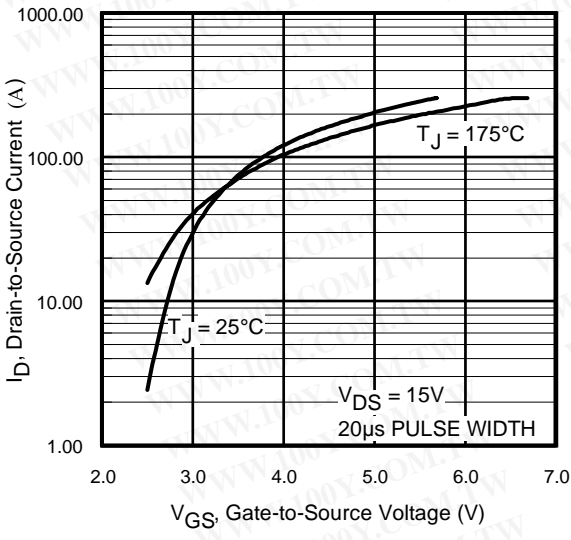


Fig 3. Typical Transfer Characteristics

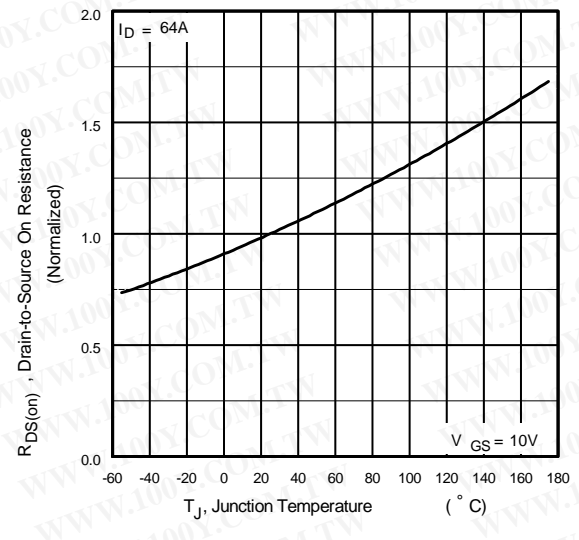


Fig 4. Normalized On-Resistance Vs. Temperature

IRLR7811WCPbF

International
IR Rectifier

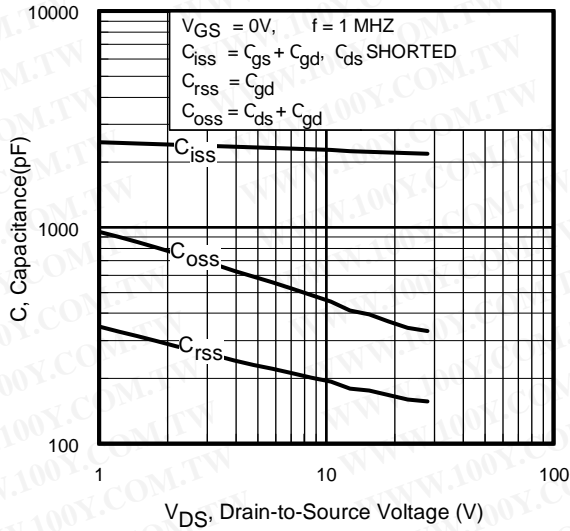


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

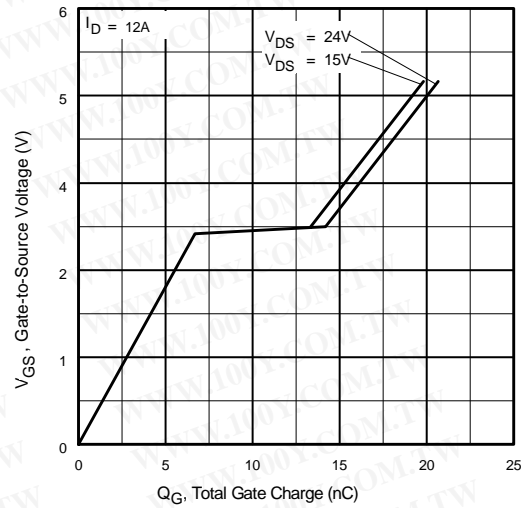


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

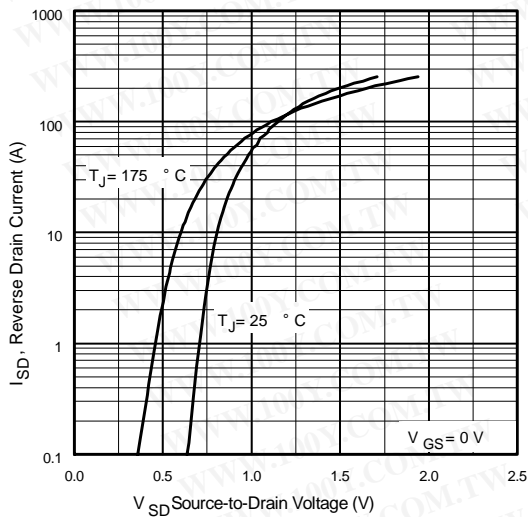


Fig 7. Typical Source-Drain Diode Forward Voltage

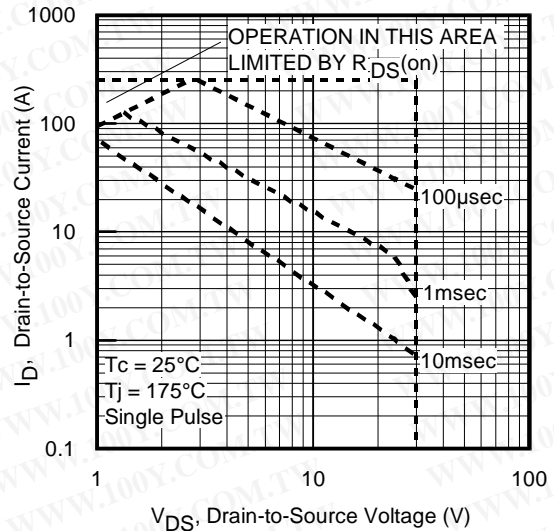


Fig 8. Maximum Safe Operating Area

International
IR Rectifier

IRLR7811WCPbF

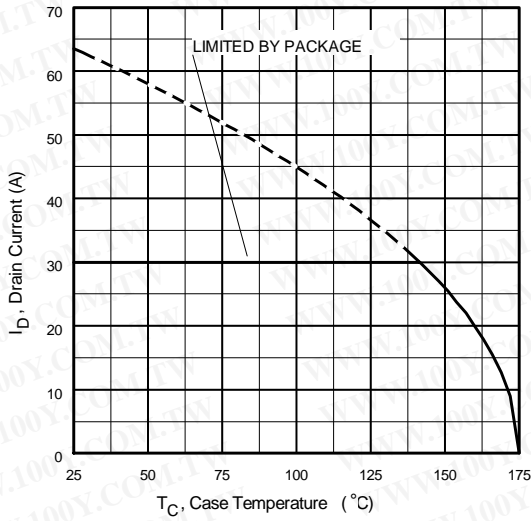


Fig 9. Maximum Drain Current Vs. Case Temperature

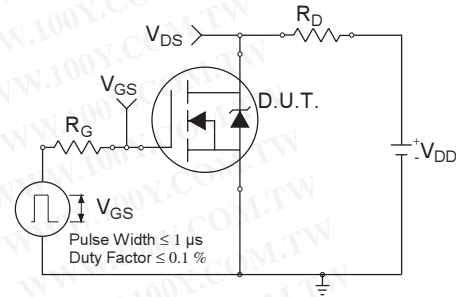


Fig 10a. Switching Time Test Circuit

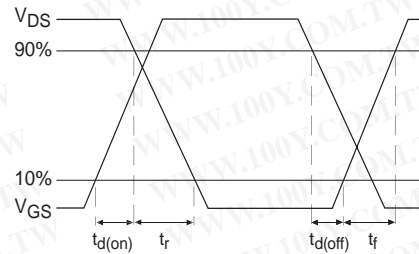


Fig 10b. Switching Time Waveforms

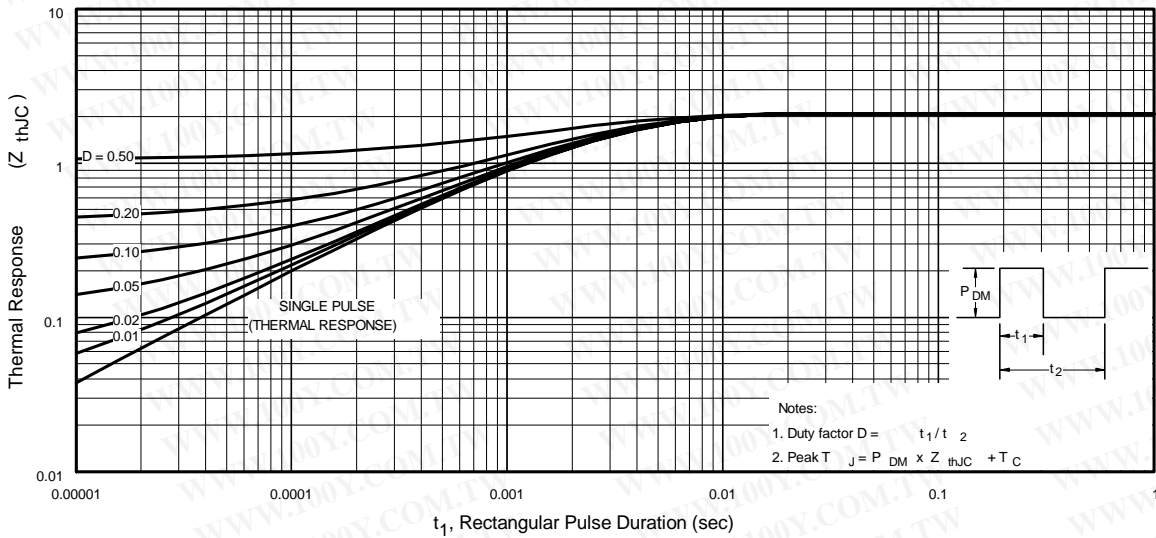


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRLR7811WCPbF

International
IRF Rectifier

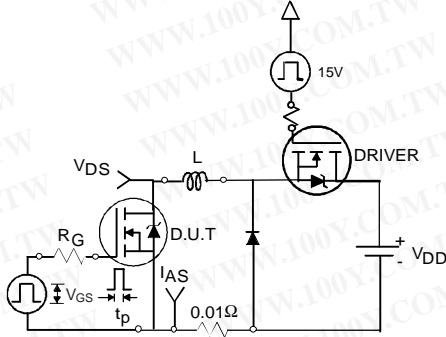


Fig 12a. Unclamped Inductive Test Circuit

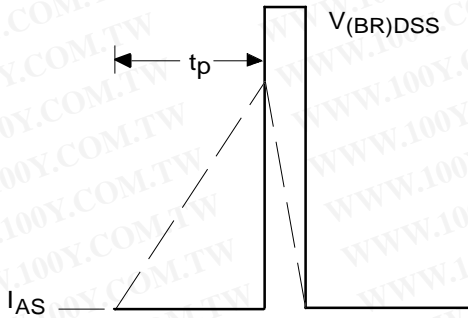


Fig 12b. Unclamped Inductive Waveforms

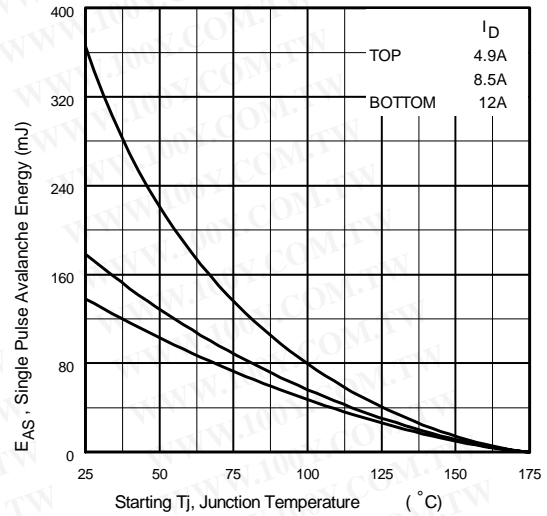


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

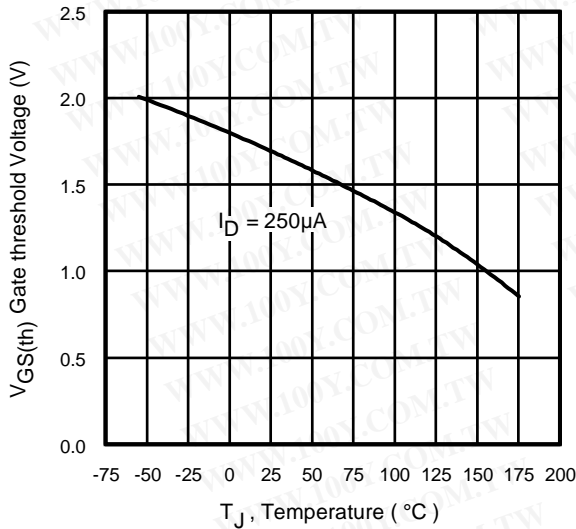


Fig 13. Threshold Voltage Vs. Temperature

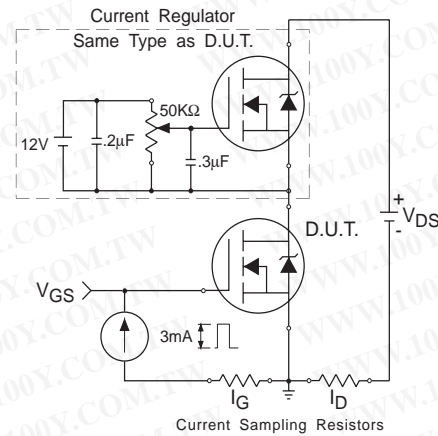
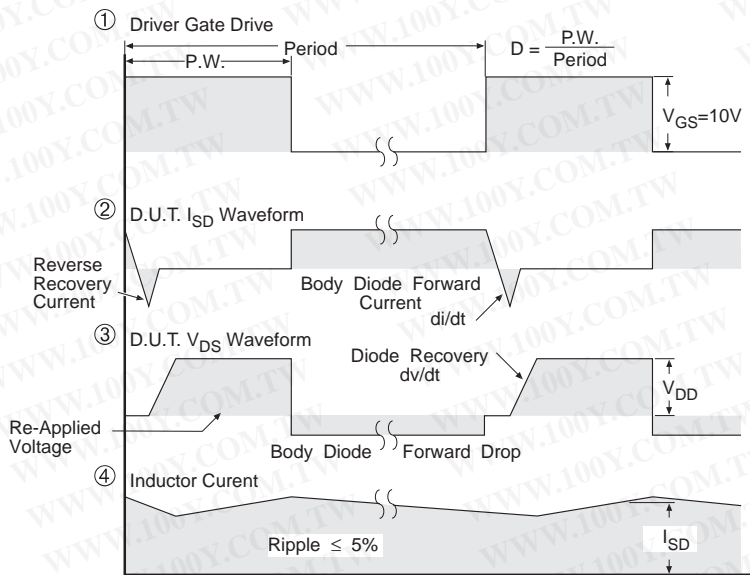
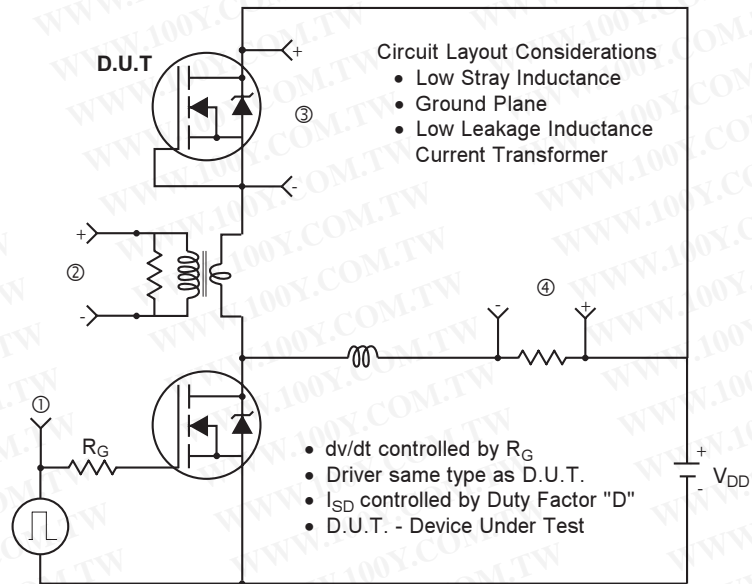


Fig 14. Gate Charge Test Circuit

IRLR7811WCPbF

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

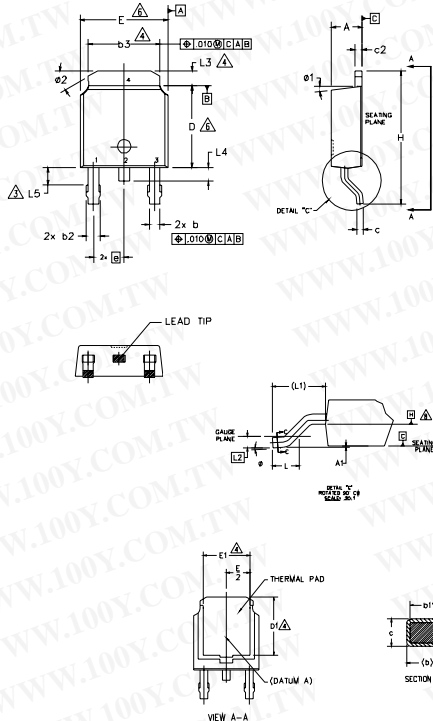
Fig 15. For N-Channel HEXFET® Power MOSFETs

IRLR7811WCPbF

International
IR Rectifier

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
 - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
 - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
 - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

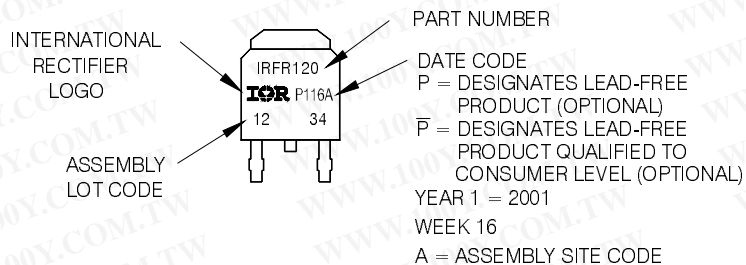
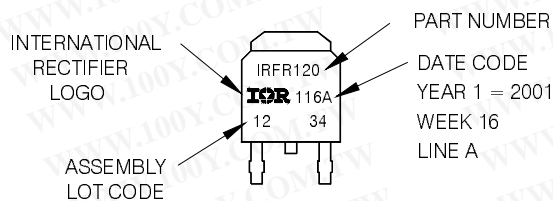
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
 WITH ASSEMBLY
 LOT CODE 1234
 ASSEMBLED ON WW 16, 2001
 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"
 "P" in assembly line position indicates "Lead-Free" qualification to the Consumer-level

OR

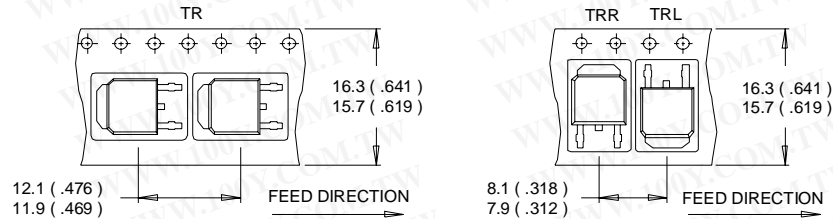


International
IR Rectifier

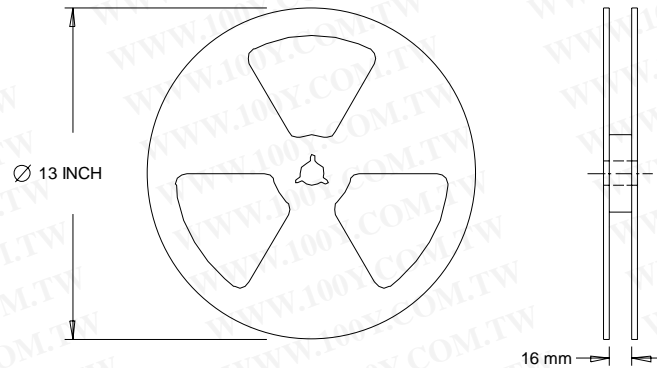
IRLR7811WCPbF

D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION: MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
 - ② Starting $T_J = 25^\circ\text{C}$, $L = 1.9\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 12\text{A}$.
 - ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
 - ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- * When mounted on 1" square PCB (FR-4 or G-10 Material).
 For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 05/2006

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)